Arima Optoelectronics
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Cat No.: 7-1S-2000-052
Revision: 0

AlInGaP LED DICE

Part NO.: AOC-S12OxM-65 Series

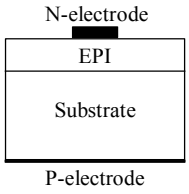
Features

- Orange color emission
- Excellent performance and high efficiency
- Great reliability even in harsh environment
- Mirror reflector to increase efficiency

Description

AOC-S12OxM-65 series is a orange color emitting AlInGaP LED grown by MOCVD technique. Its structure enables enhanced quantum efficiency; the mirror reflector greatly increases the light extraction efficiency and therefore a greater light intensity. This device is designed for ultra-high brightness (UHB) automobile, display, and consumer electronic applications.

Chip Dimensions



Chip Size：290μm×290μm ± 25μm
Bonding Pad：ϕ 105μm ±10μm
Chip Thickness : 165μm ± 25μm

Electrical and Optics Characteristics

Measuring Item	Symbol	Condition	Min	Typ.	Max	Unit
Forward Voltage	V_F	I_F=20mA	1.75	-	2.40	V
Reverse Current	I_R	V_R=5V	-	-	1.0	μA
Dominant Wavelength	λd	I_F=20mA	600	-	620	nm
Max. Junction Temperature	T_{max}	-	≦ 120			℃
Max. DC forward current	I_f	Ta = 25℃	≦ 50			mA
Max. pulse forward current (Pulse width 0.1 msec, frequency=1 kHz.)	I_{fm}	Ta = 25℃	≦ 100			mA
Storage temperature	T_{stg}	Chip on tape	0 ~ 40			℃
		Only chip	-40 ~ 80			

Available Dominate Wavelength and Iv Matrix

Part No.	Wavelength Range	≥460 mcd	≥520 mcd	≥600 mcd	≥700 mcd	≥800 mcd
S12OSM-65	600~610 nm	-	-	Y60	Y70	Y80
S12OLM-65	610~620 nm	-	Y52	Y60	Y70	-

Note:
1. All measurements are done with AOC's standard testing equipment.
2. Luminance intensity is measured on bare chip.
3. Above contents are subject to change without notice.
4. Special requests are also welcome, please contact AOC's sale representative for any request.
5. Characteristics curves are measured within TO-46 package.

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